Christian M Wetzel

List of Publications by Year
in descending order

189 papers	4,693 citations	117625 34 h-index	110387 64 g-index
189 all docs	189 docs citations	189 times ranked	3345 citing authors

#	Article	IF	Citations
1	Determination of piezoelectric fields in strained GaInN quantum wells using the quantum-confined Stark effect. Applied Physics Letters, 1998, 73, 1691-1693.	3.3	596
2	On pâ€type doping in GaNâ€”acceptor binding energies. Applied Physics Letters, 1995, 67, 1298-1300.	3.3	262
3	Pressure Induced Deep Gap State of Oxygen in GaN. Physical Review Letters, 1997, 78, 3923-3926.	7.8	223
4	Defect-reduced green GaInN/GaN light-emitting diode on nanopatterned sapphire. Applied Physics Letters, 2011, 98, .	3.3	186
5	Reduction of Etch Pit Density in Organometallic Vapor Phase Epitaxy-Grown GaN on Sapphire by Insertion of a Low-Temperature-Deposited Buffer Layer between High-Temperature-Grown GaN. Japanese Journal of Applied Physics, 1998, 37, L316-L318.	1.5	184
6	Optical band gap in Ga1âˆ’xInxNâ€Š(0<x<0.2) on GaN by photoreflection spectroscopy. Applied Physics Letters, 1998, 73, 1994-1996.	3.3	184
7	Structural properties of InN on GaN grown by metalorganic vapor-phase epitaxy. Journal of Applied Physics, 1999, 85, 7682-7688.	2.5	108
8	Anomalous features in the optical properties of Al1âˆ’xInxN on GaN grown by metal organic vapor phase epitaxy. Applied Physics Letters, 2000, 76, 876-878.	3.3	108
9	Structural and optical properties of AlInN and AlGaInN on GaN grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1998, 195, 309-313.	1.5	94
10	Monolithic integration of light-emitting diodes and power metal-oxide-semiconductor channel high-electron-mobility transistors for light-emitting power integrated circuits in GaN on sapphire substrate. Applied Physics Letters, 2013, 102, .	3.3	90
11	Piezoelectric Franzâ€“Keldysh effect in strained GaInN/GaN heterostructures. Journal of Applied Physics, 1999, 85, 3786-3791.	2.5	86
12	GaN epitaxial layers grown on 6Hâ€Šâ€“SiC by the sublimation sandwich technique. Applied Physics Letters, 1994, 65, 1033-1035.	3.3	84
13	Control of Dislocations and Stress in AlGaN on Sapphire Using a Low Temperature Interlayer. Physica Status Solidi (B): Basic Research, 1999, 216, 683-689.	1.5	80
14	Dynamics of boundâ€exciton luminescences from epitaxial GaN. Applied Physics Letters, 1996, 68, 415-417.	3.3	78
15	Carrier localization of as-grownn-type gallium nitride under large hydrostatic pressure. Physical Review B, 1996, 53, 1322-1326.	3.2	76
16	Ultrasensitive tunability of the direct bandgap of 2D InSe flakes via strain engineering. 2D Materials, 2018, 5, 021002.	4.4	75
17	GaInNâ•GaN growth optimization for high-power green light-emitting diodes. Applied Physics Letters, 2004, 85, 866-868.	3.3	71
18	Green light emitting diodes on a-plane GaN bulk substrates. Applied Physics Letters, 2008, 92, .	3.3	69

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19	Strongly localized excitons in gallium nitride. Applied Physics Letters, 1996, 68, 2556-2558.	3.3	65
20	Light-emitting diode development on polar and non-polar GaN substrates. Journal of Crystal Growth, 2008, 310, 3987-3991.	1.5	62
21	Wavelength-stable cyan and green light emitting diodes on nonpolar m-plane GaN bulk substrates. Applied Physics Letters, 2010, 96, .	3.3	59
22	Electric-field strength, polarization dipole, and multi-interface band offset in piezoelectricGa1â^'xInxN/GaNquantum-well structures. Physical Review B, 2000, 61, 2159-2163.	3.2	58
23	Carrier localization and nonradiative recombination in yellow emitting InGaN quantum wells. Applied Physics Letters, 2010, 96, .	3.3	52
24	Electron effective mass and nonparabolicity inGa0.47In0.53As/InP quantum wells. Physical Review B, 1996, 53, 1038-1041.	3.2	50
25	Quantized states inGa1â^'xInxN/GaNheterostructures and the model of polarized homogeneous quantum wells. Physical Review B, 2000, 62, R13302-R13305.	3.2	50
26	Dependence on quantum confinement of the in-plane effective mass inGa0.47In0.53As/InP quantum wells. Physical Review B, 1992, 45, 14052-14056.	3.2	47
27	Conduction-band spin splitting of type-IGaxIn1â^'xAs/InP quantum wells. Physical Review B, 1994, 49, 14786-14789.	3.2	44
28	Very high quality AlN grown on (0001) sapphire by metal-organic vapor phase epitaxy. Applied Physics Letters, 2006, 89, 103106.	3.3	44
29	GaN Based Laser Diode with Focused Ion Beam Etched Mirrors. Japanese Journal of Applied Physics, 1998, 37, L444-L446.	1.5	43
30	Properties of GaN grown at high rates on sapphire and on 6Hâ€“SiC. Applied Physics Letters, 1996, 69, 2716-2718.	3.3	39
31	Junction Temperature Measurements and Thermal Modeling of GaInN/GaN Quantum Well Light-Emitting Diodes. Journal of Electronic Materials, 2008, 37, 607-610.	2.2	39
32	Infrared reflection of GaN and AlGaN thin film heterostructures with AlN buffer layers. Applied Physics Letters, 1996, 68, 2547-2549.	3.3	37
33	Green cubic GaInN/GaN light-emitting diode on microstructured silicon (100). Applied Physics Letters, 2013, 103, .	3.3	37
34	Structural Properties of Al 1- xIn xN Ternary Alloys on GaN Grown by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L697-L699.	1.5	36
35	Microwave and far-infrared induced optically detected cyclotron resonance in epitaxial InP and GaAs. Physical Review B, 1992, 45, 1504-1506.	3.2	35
36	On the reliable analysis of indium mole fraction within InxGa1â^'xN quantum wells using atom probe tomography. Applied Physics Letters, 2014, 104, 152102.	3.3	35

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37	Enhanced Light Emission from the Ridge of Two-Dimensional InSe Flakes. Nano Letters, 2018, 18, 5078-5084.	9.1	35
38	Effect of a random adiabatic potential on the optical properties of two-dimensional excitons. Physical Review B, 1995, 52, 8384-8390.	3.2	34
39	Observation of photoluminescence from Al1âˆ’xInxN heteroepitaxial films grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1998, 73, 830-831.	3.3	34
40	Highly Polarized Green Light Emitting Diode inm-Axis GaInN/GaN. Applied Physics Express, 2010, 3, 102103.	2.4	29
41	Inclined dislocation-pair relaxation mechanism in homoepitaxial green GaInN/GaN light-emitting diodes. Physical Review B, 2010, 81, .	3.2	29
42	Piezoelectric Stark-like Ladder in GaN/GaInN/GaN Heterostructures. Japanese Journal of Applied Physics, 1999, 38, L163-L165.	1.5	28
43	Optical and structural properties of InGaN/GaN multiple quantum well structure grown by metalorganic chemical vapor deposition. Thin Solid Films, 2006, 498, 123-127.	1.8	28
44	Junction temperature, spectral shift, and efficiency in GaInN-based blue and green light emitting diodes. Thin Solid Films, 2010, 518, 1732-1736.	1.8	28
45	Development of High Power Green Light Emitting Diode Chips. MRS Internet Journal of Nitride Semiconductor Research, 2005, 10, 1.	1.0	27
46	Dislocation analysis in homoepitaxial GaInN/GaN light emitting diode growth. Journal of Crystal Growth, 2007, 298, 272-275.	1.5	27
47	On reliability and sensitivity methods for vehicle systems under stochastic crosswind loads. Vehicle System Dynamics, 2010, 48, 79-95.	3.7	27
48	Application of microwave detection of the Shubnikovâ€“de Haas effect in twoâ€dimensional systems. Journal of Applied Physics, 1993, 73, 7533-7542.	2.5	26
49	On the Bandstructure in GaInN/GaN Heterostructures - Strain, Band Gap and Piezoelectric Effect. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	26
50	A probabilistic approach for assessing the crosswind stability of ground vehicles. Vehicle System Dynamics, 2010, 48, 411-428.	3.7	26
51	Spin dependent recombination in Ptâ€doped siliconpâ€njunctions. Applied Physics Letters, 1992, 60, 1857-1859.	3.3	24
52	Fine Structure of the 3.42 eV Emission Band in GaN. Materials Research Society Symposia Proceedings, 1995, 395, 571.	0.1	23
53	Various misfit dislocations in green and yellow GaInN/GaN light emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1305-1308.	1.8	21
54	Wavelength-stable rare earth-free green light-emitting diodes for energy efficiency. Optics Express, 2011, 19, A962.	3.4	19

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55	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703.	3.3	19
56	High temperature characteristics of monolithically integrated LED and MOSâ€channel HEMT in GaN using selective epi removal. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1110-1115.	1.8	19
57	Electron effective mass in direct-band-gapGaAs1âˆ'xPxalloys. Physical Review B, 1993, 47, 15588-15592.	3.2	18
58	Optical Absorption in Polarized Ga1-xInxN/GaN Quantum Wells. Japanese Journal of Applied Physics, 2002, 41, 11-14.	1.5	18
59	Green Emitting Cubic GaInN/GaN Quantum Well Stripes on Micropatterned Si(001) and Their Strain Analysis. Advanced Electronic Materials, 2016, 2, 1500327.	5.1	18
60	Communicating Two States in Perovskite Revealed by Time-Resolved Photoluminescence Spectroscopy. Scientific Reports, 2018, 8, 16482.	3.3	18
61	Future challenges and directions for nitride materials and light emitters. Proceedings of the IEEE, 1997, 85, 1750-1751.	21.3	17
62	The quantum efficiency of green GaInN/GaN light emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 9-12.	0.8	17
63	Composition dependence of the inâ€plane effective mass in latticeâ€mismatched, strained Ga1âˆ'xInxAs/InP single quantum wells. Applied Physics Letters, 1993, 63, 657-659.	3.3	16
64	Localized Donors in Gan: Spectroscopy Using Large Pressures. Materials Research Society Symposia Proceedings, 1997, 482, 533.	0.1	16
65	Improved performance of GaInN based deep green light emitting diodes through Vâ€defect reduction. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2207-2209.	0.8	16
66	Junction temperature analysis in green light emitting diode dies on sapphire and GaN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2247-2249.	0.8	16
67	Boosting Green GaInN/GaN Light-Emitting Diode Performance by a GaInN Underlying Layer. IEEE Transactions on Electron Devices, 2010, 57, 2639-2643.	3.0	16
68	Localized vibrational modes in GaN:O tracing the formation of oxygenDX-like centers under hydrostatic pressure. Physical Review B, 2000, 61, 8202-8206.	3.2	15
69	Optimization of High-Quality AlN Epitaxially Grown on (0001) Sapphire by Metal-Organic Vapor-Phase Epitaxy. Journal of Electronic Materials, 2007, 36, 533-537.	2.2	14
70	Enhanced device performance of GaInNâ€based deep green light emitting diodes with Vâ€defectâ€free active region. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S840.	0.8	14
71	Growth and characterization of green GaInN-based light emitting diodes on free-standing non-polar GaN templates. Journal of Crystal Growth, 2009, 311, 2937-2941.	1.5	14
72	Evaluation of metal/indium-tin-oxide for transparent low-resistance contacts to p-type GaN. Applied Optics, 2012, 51, 5596.	1.8	14

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73	High 400â€‰Â°C operation temperature blue spectrum concentration solar junction in GaInN/GaN. Applied Physics Letters, 2014, 105, .	3.3	14
74	Si in GaN â€" On the Nature of the Background Donor. Physica Status Solidi (B): Basic Research, 1996, 198, 243-249.	1.5	13
75	DX-like behavior of oxygen in GaN. Physica B: Condensed Matter, 2001, 302-303, 23-38.	2.7	13
76	Electron-Phonon Scattering in Si-Doped GaN. Materials Research Society Symposia Proceedings, 1996, 449, 567.	0.1	12
77	Piezoelectric Polarization in GaInN/GaN Heterostructures and Some Consequences for Device Design. Japanese Journal of Applied Physics, 2000, 39, 2425-2427.	1.5	12
78	Improvement of Crystalline Quality of Group III Nitrides on Sapphire Using Low Temperature Interlayers. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 870-877.	1.0	11
79	Photoluminescence of GaInN/GaN multiple quantum well heterostructures on amorphous surface through biaxial metal buffer layers. Nano Energy, 2014, 5, 1-8.	16.0	11
80	Monolithically Integrated GaN LED/Quasi-Vertical Power U-Shaped Trench-Gate MOSFET Pairs Using Selective Epi Removal. IEEE Electron Device Letters, 2019, 40, 1736-1739.	3.9	11
81	Heteroepitaxy of Group III Nitrides for Device Applications. Materials Science Forum, 1998, 264-268, 1115-1120.	0.3	10
82	Wavelength-resolved low-frequency noise of GaInNâˆ•GaN green light emitting diodes. Journal of Applied Physics, 2006, 100, 084506.	2.5	10
83	Vâ€defect analysis in green and deep green light emitting diode structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1777-1779.	0.8	10
84	Characterization of GaInN/GaN layers for green emitting laser diodes. Journal of Crystal Growth, 2009, 311, 2942-2947.	1.5	10
85	Incorporation of indium on cubic GaN epitaxially induced on a nanofaceted Si(001) substrate by phase transition. Applied Physics Letters, 2015, 107, .	3.3	10
86	Optimizing GaInN/GaN light-emitting diode structures under piezoelectric polarization. Journal of Applied Physics, 2017, 122, .	2.5	10
87	GaN On 6H-SiC â€" Structural And Optical Properties. Materials Research Society Symposia Proceedings, 1994, 339, 453.	0.1	9
88	Optically detected cyclotron resonance on GaAs/AlxGa1âˆ’xAs quantum wells and quantum wires. Physical Review B, 1995, 52, 11313-11318.	3.2	9
89	GaN-based laser diode with focused ion beam-etched mirrors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 382-385.	3.5	9
90	Discrete Steps in the Capacitance-Voltage Characteristics of GaInN/GaN Light Emitting Diode Structures. Materials Research Society Symposia Proceedings, 2004, 831, 449.	0.1	9

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91	Optimization of green and deep green GaInN/GaN light emitting diodes for homogeneity. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2871-2873.	0.8	9
92	Valence band splitting and luminescence Stokes shift in GaInN/GaN thin films and multiple quantum well structures. Journal of Crystal Growth, 1998, 189-190, 621-624.	1.5	8
93	Effects of oxygen thermal annealing treatment on formation of ohmic contacts to n-GaN. Applied Physics Letters, 2012, 101, .	3.3	8
94	High Quality Interfaces in a-Si:H/a-Sic:H Superlattices. Materials Research Society Symposia Proceedings, 1990, 192, 237.	0.1	7
95	X-Ray Photoelectron Diffraction Measurements of Hexagonal GaN(0004) Thin Films. Materials Research Society Symposia Proceedings, 1997, 468, 263.	0.1	7
96	Piezoelectric Quantization in GaInN thin Films and Multiple Quantum Well Structures. Materials Research Society Symposia Proceedings, 1998, 512, 181.	0.1	7
97	Radiation damage mechanisms for luminescence in Eu-doped GaN. Journal of Applied Physics, 2007, 101, 054902.	2.5	7
98	Photothermal deflection spectroscopy as a method for studying quantum-well heterostructures. Superlattices and Microstructures, 1989, 6, 99-102.	3.1	6
99	Novel applications of contactless characterization techniques in epitaxial crystals and quantum well structures. Journal of Crystal Growth, 1993, 128, 567-570.	1.5	6
100	The conduction band spin splitting in type-I strained and unstrained (GaIn)As/InP quantum wells. Solid-State Electronics, 1994, 37, 669-672.	1.4	6
101	Structural Characterization of Homoepitaxial Blue GaInN/GaN Light-Emitting Diodes by Transmission Electron Microscopy. Journal of Electronic Materials, 2008, 37, 641-645.	2.2	6
102	Radiation Effects on InGaN Quantum Wells and GaN Simultaneously Probed by Ion Beam-Induced Luminescence. IEEE Transactions on Nuclear Science, 2008, 55, 3633-3637.	2.0	6
103	Analysis of the stability of InGaN/GaN multiquantum wells against ion beam intermixing. Nanotechnology, 2015, 26, 425703.	2.6	6
104	Effect of InGaN/GaN superlattice as underlayer on characteristics of AlGaN/GaN HEMT. AIP Advances, 2020, 10, 025133.	1.3	6
105	Time Resolved Photoluminescence Spectroscopy on GaN Epitaxial Layers. Materials Research Society Symposia Proceedings, 1995, 378, 521.	0.1	5
106	Defect Studies of GaN under Large Hydrostatic Pressure. Materials Research Society Symposia Proceedings, 1995, 395, 417.	0.1	5
107	Absorption Spectroscopy and Band Structure in Polarized GaN/AlxGa1?xN Quantum Wells. Physica Status Solidi A, 2001, 183, 51-60.	1.7	5
108	Temperature dependence of the quantum efficiency in green light emitting diode dies. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2784-2787.	0.8	5

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109	Depth profile of donorâ€“acceptor pair transition revealing its effect on the efficiency of green LEDs. Physica B: Condensed Matter, 2009, 404, 4899-4902.	2.7	5
110	Green LED development in polar and non-polar growth orientation. Proceedings of SPIE, 2009, , .	0.8	5
111	Atomic-Scale Phase Transition of Epitaxial GaN on Nanostructured Si(001): Activation and Beyond. Crystal Growth and Design, 2016, 16, 2183-2189.	3.0	5
112	Exploring swift-heavy ion irradiation of InGaN/GaN multiple quantum wells for green-emitters: the use of Raman and photoluminescence to assess the irradiation effects on the optical and structural properties. Journal of Materials Chemistry C, 2021, 9, 8809-8818.	5.5	5
113	Recombination dynamics in strained In1-xGaxAs/InP-quantum well structures. Superlattices and Microstructures, 1994, 15, 303.	3.1	4
114	Photoluminescence Studies of GaN and AlGaN Layers Under Hydrostatic Pressure. Materials Research Society Symposia Proceedings, 1995, 378, 509.	0.1	4
115	Identification of Transition Metals in GaN. Materials Research Society Symposia Proceedings, 1995, 395, 491.	0.1	4
116	Optical investigation of deep defects in GaN epitaxial layers grown on 6H-SiC. Materials Science and Technology, 1996, 12, 90-93.	1.6	4
117	Discrete Stark-Like Ladder in Piezoelectric GaInN/GaN Quantum Wells. Physica Status Solidi (B): Basic Research, 1999, 216, 399-403.	1.5	4
118	Piezoelectric polarization in the radiative centers of GaInN/GaN quantum wells and devices. Journal of Electronic Materials, 2000, 29, 252-255.	2.2	4
119	Analysis of the wavelength-power performance roll-off in green light emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2421-2424.	0.8	4
120	Optical and structural investigation on InGaN/GaN multiple quantum well light-emitting diodes grown on sapphire by metalorganic chemical vapor deposition. , 2006, 6337, 38.		4
121	Cyan and green light emitting diode on nonâ€polar m â€plane GaN bulk substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2190-2192.	0.8	4
122	Two-dimensional wannier excitons. Effects of a random adiabatic potential. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1447-1452.	0.4	3
123	Correlation of vibrational modes and DX-like centers in GaN:O. Physica B: Condensed Matter, 1999, 273-274, 109-112.	2.7	3
124	Defect and Stress Control of Algan and Fabrication of High-Efficiency Uv-Led. Materials Research Society Symposia Proceedings, 2000, 639, 1271.	0.1	3
125	Ultrafast Carrier Dynamics and Recombination in Green Emitting InGaN MQW LED. Materials Research Society Symposia Proceedings, 2006, 916, 10.	0.1	3
126	Phosphor-free white: the prospects for green direct emitters. Proceedings of SPIE, 2011, , .	0.8	3

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127	The role of mesa size in nanoâ€structured green AlGaInN lightâ€emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2311-2314.	0.8	3
128	Quantitative Chemical Mapping of InGaN Quantum Wells from Calibrated High-Angle Annular Dark Field Micrographs. Microscopy and Microanalysis, 2015, 21, 994-1005.	0.4	3
129	Improved electrical performance of MOCVD-grown GaN p-i-n diodes with high-low junction p-layers. Solid-State Electronics, 2019, 162, 107646.	1.4	3
130	Photothermal deflection spectroscopy of InGaAs/InP quantum wells. Semiconductor Science and Technology, 1990, 5, 702-706.	2.0	2
131	Spin Dependent Recombination at Deep Centers in Si - Electrically Detected Magnetic Resonance. Materials Science Forum, 0, 83-87, 1165-1170.	0.3	2
132	Structural Properties of Nitrides Grown by Omvpe on Sapphire Substrate. Materials Research Society Symposia Proceedings, 1997, 482, 523.	0.1	2
133	Characterization of the crystalline quality on GaN on sapphire and ternary alloys. Electronics and Communications in Japan, 1998, 81, 48-54.	0.2	2
134	Current and optical low-frequency noise of GaInN/GaN green light emitting diodes. , 2007, 6600, 174.		2
135	Photon modulated electroluminescence of GaInN/GaN multiple quantum well light emitting diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2293-2295.	0.8	2
136	Non-polar GaInN-based light-emitting diodes: an approach for wavelength-stable and polarized-light emitters. , 2011, , .		2
137	INTEGRATION OF N- AND P-CONTACTS TO GaN-BASED LIGHT EMITTING DIODES. International Journal of High Speed Electronics and Systems, 2011, 20, 521-525.	0.7	2
138	HOW DO WE LOSE EXCITATION IN THE GREEN?. International Journal of High Speed Electronics and Systems, 2011, 20, 13-25.	0.7	2
139	Rare-Earth-Free Direct-Emitting Light-Emitting Diodes for Solid-State Lighting. IEEE Transactions on Industry Applications, 2014, 50, 1469-1477.	4.9	2
140	Initial stage of cubic GaN for heterophase epitaxial growth induced on nanoscale v-grooved Si(001) in metal-organic vapor-phase epitaxy. Nanotechnology, 2019, 30, 025711.	2.6	2
141	Properties of Gainasp Alloys Investigated by Optically Detected Macnetic Resonance Techniques. Materials Research Society Symposia Proceedings, 1990, 216, 353.	0.1	1
142	Magneto-optical and far-infrared optically detected cyclotron resonance determination of the effective mass in GaAs1â^'xPx. Physica B: Condensed Matter, 1993, 184, 164-167.	2.7	1
143	Optical transitions in piezoelectrically polarized GaInN/GaN quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 216.	1.6	1
144	Structural Analysis in Low-V-defect Blue and Green GaInN/GaN Light Emitting Diodes. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	1

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145	LOW TEMPERATURE ELECTROLUMINESCENCE OF GREEN AND DEEP GREEN GaInN/GaN LIGHT EMITTING DIODES. International Journal of High Speed Electronics and Systems, 2007, 17, 25-28.	0.7	1
146	Very strong nonlinear optical absorption in green GaInN/GaN multiple quantum well structures. Physica Status Solidi (B): Basic Research, 2008, 245, 916-919.	1.5	1
147	GaN-based light emitting diode with embedded SiO<inf>2</inf> pattern for enhanced light extraction. , 2012, , .		1
148	Direct green LED development in nano-patterned epitaxy. , 2013, , .		1
149	Nanopatterned epitaxy of non-polar Ga1-yInyN layers with caps and voids. Journal of Applied Physics, 2017, 122, 094303.	2.5	1
150	LOW TEMPERATURE ELECTROLUMINESCENCE OF GREEN AND DEEP GREEN GaInN/GaN LIGHT EMITTING DIODES. , 2007, , .		1
151	Cubic GaInN/GaN Multi-Quantum Wells for Increased Smart Lighting System Efficiency. , 2012, , .		1
152	Photoluminescence and optically detected impact ionization studies of GaInAs/InP strained layer superlattices. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1991, 9, 293-296.	3.5	0
153	<title>Optically detected cyclotron resonance determination of the in-plane effective mass in Ga<formula><inf><roman>0.47</roman></inf></formula>In<formula><inf><roman>0.53</roman></inf></formula>As/InP single quantum wells</title>. , 1992, , .		0
154	Modulated cyclotron resonance in multi-quantum well structure of In0.53Ga0.47As/InP induced by interband and exciton excitation. Journal of Infrared, Millimeter and Terahertz Waves, 1994, 15, 237-246.	0.6	0
155	Carrier Localization in Gallium Nitride. Materials Science Forum, 1995, 196-201, 31-36.	0.3	0
156	On the nature of radiative recombination processes in GaN. , 1997, , .		0
157	Optical properties of GaInN/GaN heterostructures and quantum wells. , 0, , .		0
158	Improvement of Crystalline Quality of Group III Nitrides on Sapphire Using Low Temperature Interlayers. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
159	Piezoelectric Level Splitting in GaInN/GaN Quantum Wells. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
160	Spectroscopy in Polarized and Piezoelectric AlGaInN Heterostructures. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	0
161	Nitride-based laser diodes using thick n-AlGaN layers. Journal of Electronic Materials, 2000, 29, 302-305.	2.2	0
162	Internal omni-directional reflector using a low refractive index material for light-emitting diodes. , 2005, , .		0

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163	Charge Profiling of the p-AlGaN Electron Blocking Layer in AlGaInN Light Emitting Diode Structures. Materials Research Society Symposia Proceedings, 2005, 892, 424.	0.1	0
164	Development of high-power green light emitting diode dies in piezoelectric GaInN/GaN. , 2005, , .		0
165	Analysis of the Quantum Efficiency of GaInN/GaN Light Emitting Diodes in the Range of 390 - 580 nm. Materials Research Society Symposia Proceedings, 2005, 892, 212.	0.1	0
166	Time resolved charge profiling of polarization dipoles in high power 525 nm green GaInN/GaN light emitting structures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1806-1810.	1.8	0
167	Low-Temperature Cathodoluminescence Mapping of Green, Blue, and UV GaInN/GaN LED Dies. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
168	Loss of Quantum Efficiency in Green Light Emitting Diode Dies at Low Temperature. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
169	Development of high efficiency green and deep green light emitters in piezoelectric group-iii nitrides. , 2007, , .		0
170	Green Light Emitting Diodes under Photon Modulation. Materials Research Society Symposia Proceedings, 2007, 1040, 1.	0.1	0
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